

TECHNICAL DAT
DATA SHEET 1008, REV. B

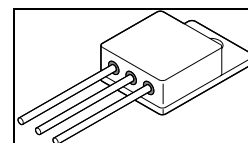
HERMETIC POWER SCHOTTKY RECTIFIER Low Forward Voltage Drop (60 V, 35A)

Applications:

- Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

Features:

- Soft Reverse Recovery at Low and High Temperature
- Low Forward Voltage Drop
- Low Reverse Leakage Current
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics



Maximum Ratings:

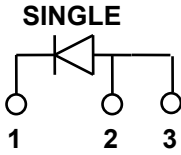
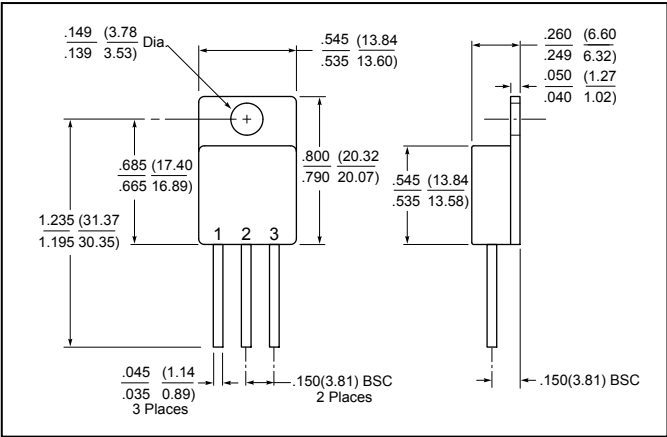
Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	60	V
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_C = 100^\circ\text{C}$, rectangular wave form	35	A
Max. Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, half Sine pulse	150	A
Max. Junction Temperature	T_J	-	-65 to +150	$^\circ\text{C}$
Max. Storage Temperature	T_{stg}	-	-65 to +175	$^\circ\text{C}$

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 35 A, Pulse, $T_J = 25^\circ\text{C}$	0.75	V
	V_{F2}	@ 35 A, Pulse, $T_J = 125^\circ\text{C}$	0.64	V
Max. Reverse Current	I_{R1}	@ $V_R = 60\text{V}$, Pulse, $T_J = 25^\circ\text{C}$	9.0	mA
	I_{R2}	@ $V_R = 60\text{V}$, Pulse, $T_J = 125^\circ\text{C}$	420	mA
Max. Junction Capacitance	C_T	@ $V_R = 5\text{V}$, $T_C = 25^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$, $V_{SIG} = 50\text{mV (p-p)}$	4800	pF
Maximum Thermal Resis.	$R_{\theta JC}$	-	0.62	$^\circ\text{C/W}$

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Mechanical Dimensions: In Inches / mm



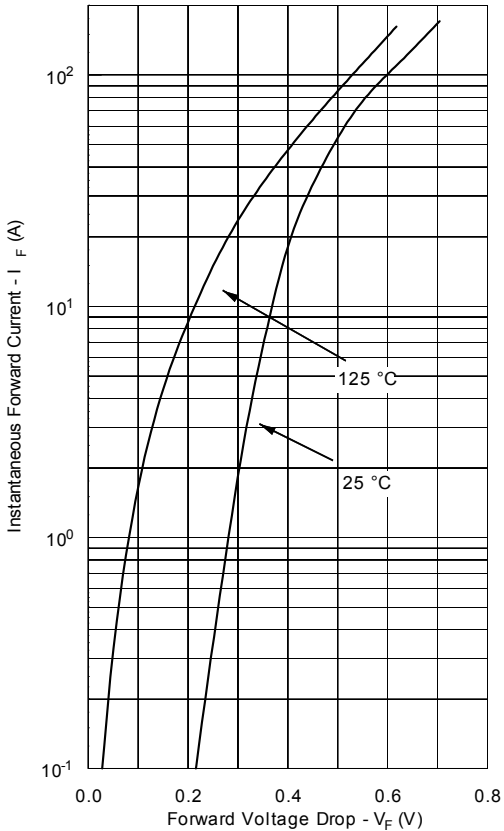
TO-254

PINOUT TABLE

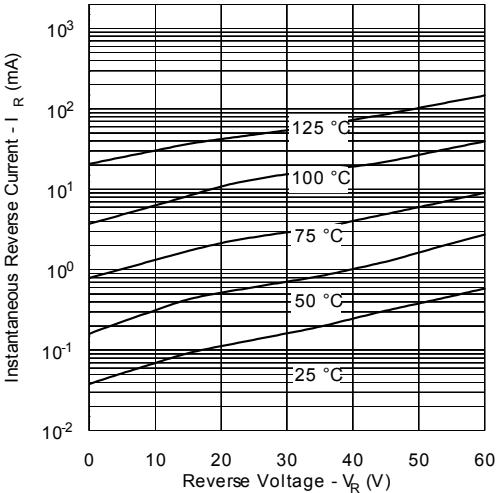
TYPE	PIN 1	PIN 2	PIN 3
SINGLE RECTIFIER	CATHODE	ANODE	ANODE

Note: The V_f curves shown are for the un-packaged die only.

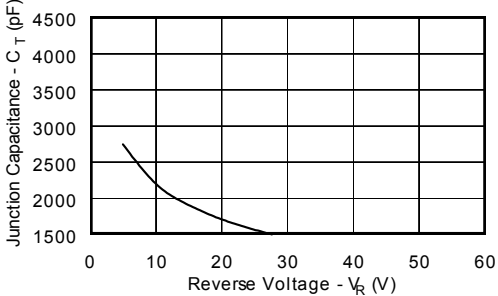
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



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